



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92MOD Plastic-Encapsulate Transistors

2SB892 TRANSISTOR (PNP)

FEATURE

Power dissipation

P_{CM} : 1 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -2 A

Collector-base voltage

$V_{(BR)CBO}$: -60 V

Operating and storage junction temperature range

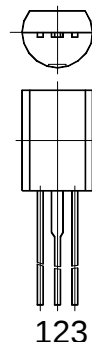
T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

TO-92MOD

1. EMITTER

2. COLLECTOR

3. BASE



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0$	-60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-50		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-6		V
Collector cut-off current	I_{CBO}	$V_{CB} = -50V, I_E = 0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4V, I_C = 0$		-0.1	μA
DC current gain	$H_{FE(1)}$	$V_{CE} = -2V, I_C = -100mA$	100	560	
	$H_{FE(2)}$	$V_{CE} = -2V, I_C = -1.5A$	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1A, I_B = -50mA$		-0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -1A, I_B = -50mA$		-1.2	V
Transition frequency	f_T	$V_{CE} = -10V, I_C = -50mA$	150		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	R	S	T	U
Range	100-200	140-280	200-400	280-560